

High power NPN epitaxial planar bipolar transistor

Preliminary data

Features

- High breakdown voltage V_{CEO} = 230 V
- Typical f_T = 30 MHz

Application

■ Audio power amplifier

Description

This device is a NPN transistor manufactured using new BiT-LA (bipolar transistor for linear amplifier) technology. The resulting transistor shows good gain linearity behaviour.

Josoleite Productils

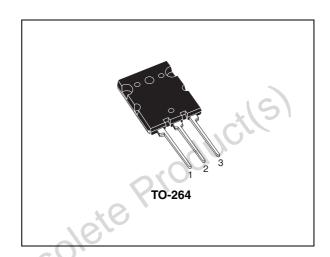


Figure 1. Internal schematic diagram

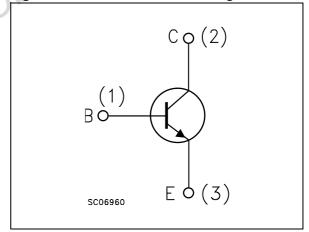


Table 1. Device summary

Order code	Marking	Package	Packaging
2SC5200	2SC5200	TO-264	Tube

September 2009 Doc ID 16310 Rev 1 1/8

Electrical ratings 2SC5200

1 Electrical ratings

Table 2. Absolute maximum ratings

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-base voltage (I _E = 0)	230	V
V_{CEO}	Collector-emitter voltage (I _B = 0)	230	V
V_{EBO}	Emitter-base voltage ($I_C = 0$)	5	V
I _C	Collector current	15	Α
I _{CM}	Collector peak current	30	А
P _{TOT}	Total dissipation at T _C = 25 °C	150	W
T _{STG}	Storage temperature	-55 to 150	°C
TJ	Operating junction temperature	150	°C

Table 3. Thermal data

	Symbol	Parameter	Value	Unit
	R_{thJC}	Thermal resistance junction-case max	0.83	°C/W
Obsole	R _{thJC} Thermal resistance junction-case max			

Electrical characteristics 2

T_{case} = 25 °C unless otherwise specified

Table 4. **Electrical characteristics**

L	Parameter	Test conditions	Min.	Тур.	Max.	Unit
I _{CBO}	Collector cut-off current (I _E = 0)	V _{CB} = 230 V			5	μΑ
I _{EBO}	Emitter cut-off current (I _C = 0)	V _{EB} = 5 V			5	μA
V _{(BR)CEO} ⁽¹⁾	Collector-emitter breakdown voltage (I _B = 0)	I _C = 50 mA	230			V
V _{(BR)CBO}	Collector-base breakdown voltage (I _E = 0)	I _C = 100 μA	230	70,		V
V _{(BR)EBO} ⁽¹⁾	Emitter-base breakdown voltage ($I_C = 0$)	I _E = 1 mA	5			V
V _{CE(sat)} ⁽¹⁾	Collector-emitter saturation voltage	I _C = 8 A I _B = 800 mA			3	V
V _{BE}	Base-emitter voltage	I _C = 7 A V _{CE} = 5 V			1.5	V
h _{FE}	DC current gain	$I_C = 1 \text{ A}$ $V_{CE} = 5 \text{ V}$ $I_C = 7 \text{ A}$ $V_{CE} = 5 \text{ V}$	55 35	80	120	
t _{on} t _s t _f	Resistive load Turn-on time Storage time Fall time	$V_{CC} = 60 \text{ V}$ $I_C = 5A$ $I_{B1} = -I_{B2} = 0.5 \text{ A}$		0.24 4.7 0.6		μs μs μs
f _T	Transition frequency	I _C = 1 A V _{CE} = 5 V		30		MHz
C _{CBO}	Collector-base capacitance (I _E = 0)	V _{CB} = 10 V f = 1 MHz		150		pF

2.1 Electrical characteristics (curves)

Figure 2. Safe operating area

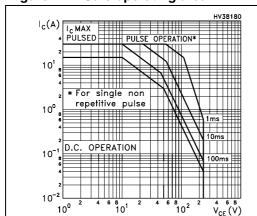
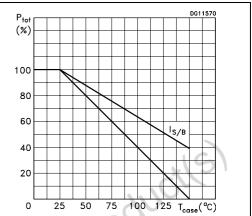
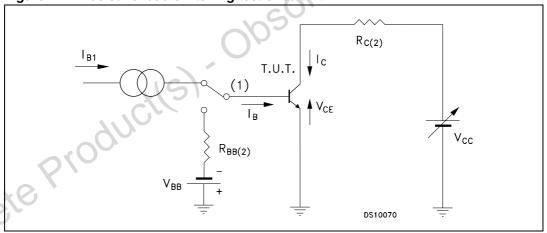


Figure 3. Derating curve



2.2 Test circuit

Figure 4. Resistive load switching test circuit



- 1. Fast electronic switch
- 2. Non-inductive resistor

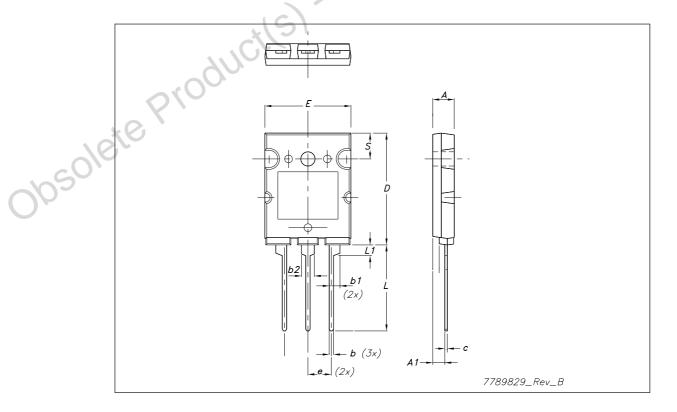
3 Package mechanical data

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TO-264 Mechanical data

Dim.		mm.	
D	Min.	Тур	Max.
Α	4.80		5.20
A1	2.50		3.10
b	0.90	1.0	1.25
b1		2.5	,(5)
b2		2.8	(C)
С	0.50	0.60	0.85
D	25.6		26.4
Е	19.80		20.20
е	5.15	9/2	5.75
L	19.50	76,	20.50
L1	2.30	1250	2.70
øΡ	3.55	103	3.65



2SC5200 Revision history

4 Revision history

Table 5. Document revision history

Date	Revision	Changes
28-Sep-2009	1	Initial release.

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